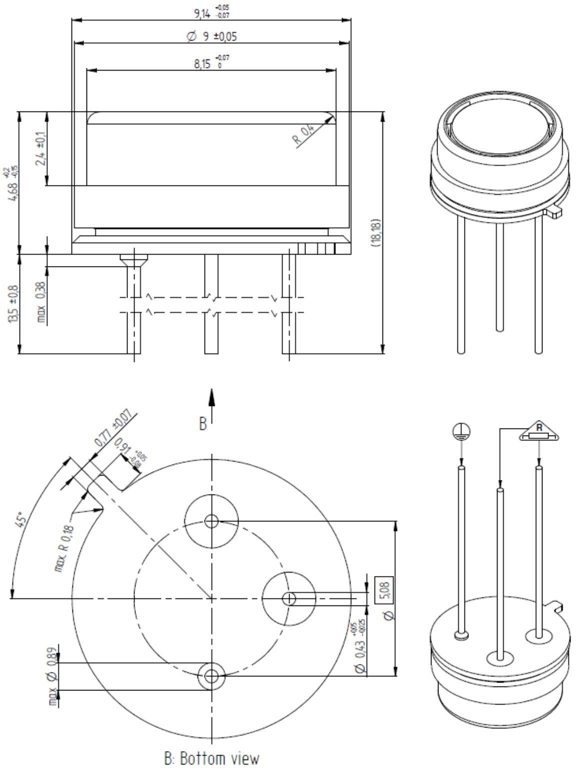
Axetris AG
Schwarzenbergstrasse 10
CH-6056 Kaegiswil
phone +41 41 662 76 76
fax +41 41 662 75 25
axetris@axetris.com
www.axetris.com

EMIRS200_AT01T_BC010_Series
EMIRS200_AT02V_BC010_Series

Thermal MEMS based infrared source

For direct electrical fast modulation

TO39 header with Reflector 4
With Germanium (AR coated), Barium Fluoride, Calcium Fluoride or Sapphire window



■ Infrared Source

Axetris infrared (IR) sources are micro-machined, electrically modulated thermal infrared emitters featuring true blackbody radiation characteristics, low power consumption, high emissivity and a long lifetime. The appropriate design is based on a resistive heating element deposited onto a thin dielectric membrane which is suspended on a micro-machined silicon structure.

■ Infrared Gas Detection Applications

- **Measurement principles:** non-dispersive infrared spectroscopy (NDIR), photoacoustic infrared spectroscopy (PAS) or attenuated-total-reflectance FTIR spectroscopy (ATR)
- **Target gases:** CO, CO_2, VOC, NO_X, NH_3, SO_X, SF_6, hydrocarbons, humidity, anesthetic agents, refrigerants, breath alcohols
- **Medical:** Capnography, anesthesia gas monitoring, respiration monitoring, pulmonary diagnostics, blood gas analysis
- **Industrial Applications:** Combustible and toxic gas detection, refrigerant monitoring, flame detection, fruit ripening monitoring, SF_6 monitoring, semi-conductor fabrication
- **Automotive:** CO_2 automotive refrigerant monitoring, alcohol detection & interlock, cabin air quality
- **Environmental:** Heating, ventilating and air conditioning (HVAC), indoor air quality and VOC monitoring, air quality monitoring

■ Features

- Large modulation depth at high frequencies
- Broad band emission
- Low power consumption
- Long lifetime
- True black body radiation (2 to 14 µm)
- Very fast electrical modulation (no chopper wheel needed)
- Suitable for portable and very small applications
- Rugged MEMS design

■ Absolute Maximum Ratings (T_A = 22°C)

Parameter	Symbol	Rating				Unit
Heater membrane temperature[1]	T_M	500				°C
Window		GeAR	BaF_2	CaF_2	Sapph.	
Optical output power (hemispherical spectral) (T_M = 500°C)	P_{00}	35	34	32	18	mW
Optical output power between 4 µm and 5 µm (T_M = 500°C)	P_{s4-5}	4.9	4.8	4.9	4.7	mW
Optical output power between 6 µm and 8 µm (T_M = 500°C)	P_{s6-8}	6.6	6.6	6.7	1.3	mW
Optical output power between 8 µm and 10 µm (T_M = 500°C)	P_{s8-10}	4.1	4.0	4.0	0.0	mW
Optical output power between 10 µm and 13 µm (T_M = 500°C)	P_{s10-13}	3.1	3.3	2.1	0.0	mW
Electrical cold resistance (at $T_M = T_A$ = 22°C)	R_{C22}	35 to 55				Ω
Electrical operating (hot) resistance[2] (at T_M = 500°C with f = ≥ 5 Hz and t_{on} ≥ 8 ms)	R_{H500C}	1.883 * RC22 – 12.02				Ω
Package temperature	T_P	80				°C
Storage temperature	T_S	-20 to +85				°C
Ambient temperature[3] (operation)	T_A	-40 to +125				°C
Heater area	A_H	2.1 x 1.8				mm²
Frequency[4]	f	5 to 50				Hz

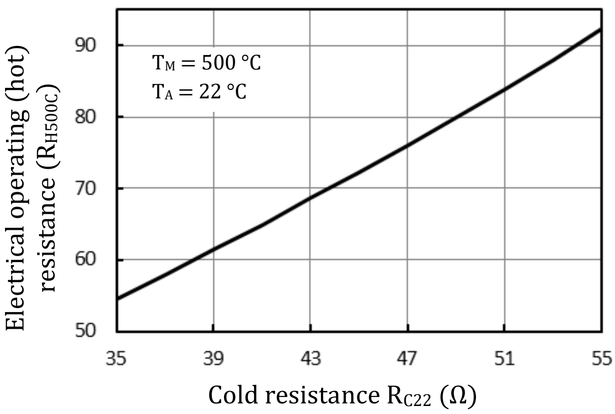
Note: Emission power in this table is defined by hemispherical radiation. Stress beyond those listed under "absolute maximum ratings" may cause permanent damage to the device.

Note: Diagram R_{H500C} — R_{C22} | (T_M = 500°C)

How to ensure that the maximum temperature for T_M is not exceeded:

1. Determine electrical cold resistance R_C of the EMIRS device at TA=22°C
2. Ensure that anytime R_H does not exceed the representative limit as shown in this diagram with respect to these conditions:
   a. f ≥ 5 Hz
   b. on-time (pulse duration) ≥ 8 ms

R_{H500C} — R_{C22}
(T_M = 500°C)



Electrical operating (hot) resistance R_H versus electrical cold resistance R_{C22} at T_A = 22°C

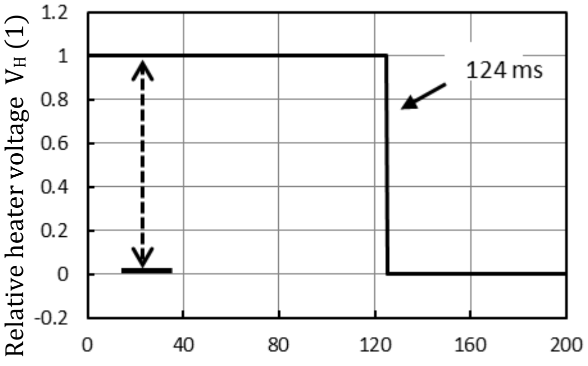
[1] Temperatures above 500°C will impact drift and lifetime of the devices.
[2] See Diagram R_H — R_C | (T_M = 500°C)
[3] The environmental and package temperature might impact the lifetime and characteristic of the devices.
[4] Lower cut-off frequency of 5 Hz for designed thermodynamic state.

■ Ratings at Reference Operation (RO[1] T_A = 22°C)

Parameter	Symbol	Rating	Unit
Heater membrane temperature	T_M	< 500	°C
Duty cycle of rectangular V_H pulse	D	62	%
Frequency of rect. pulse shape[2]	f_{ref}	5	Hz
On time constant of integral emissive power P_{OO}	τ_{on}	18	ms
Off time constant of integral emissive power P_{OO}	τ_{off}	8	ms
Package temperature at T_A = 22°C	T_P	40 to 85	°C

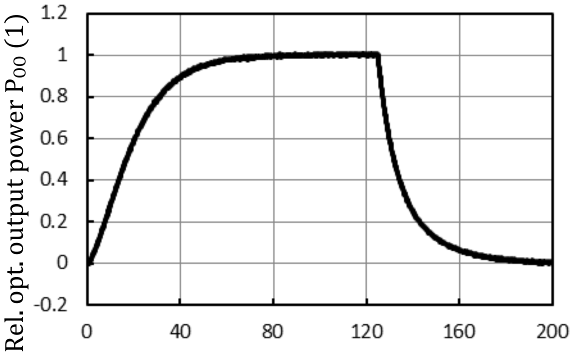
Note: First order on-time model using τ_{on}: First order off-time model using τ_{off}:

V_H — t
(RO[1] input pulse shape)



Relative rectangular heater voltage (V_H) pulse with a relative pulse width of 124 ms at 5 Hz (time description of reference operation RO[1])

P_{OO} — t
(Optical response of RO[1] input)

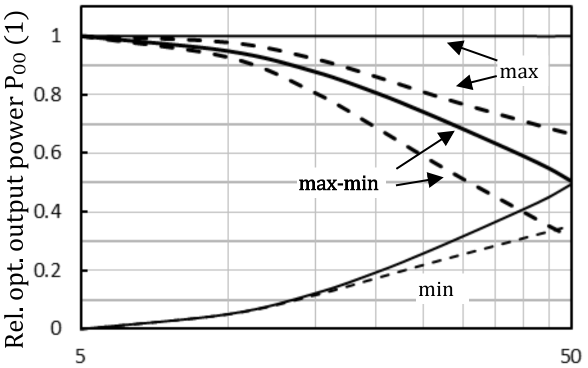


Optical response time (relative optical output power P_{OO}) of a rectangular voltage pulse (RO[1] conditions)

[1] Reference Operation: combines lower cut-off frequency of 5 Hz and maximum modulation depth (max-min signal)
[2] Recommended frequencies from 5 Hz to 50 Hz

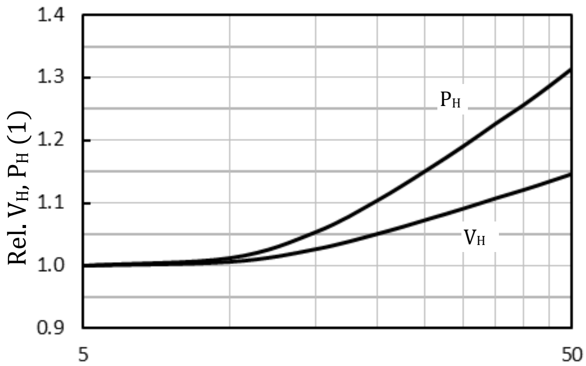
■ Typical Timing Characteristics Frequency (D = 62%)

P_{OO} - - - f (fixed V_H)
P_{OO} — f, (comp V_H)



Relative (to RO) max, min, max-min values of optical output power (P_{OO}) versus frequency f with fixed and compensated V_H

V_H, P_H — f
(compensation factor)



Relative (to RO) electrical drive values heater voltage V_H and power P_H versus frequency f for compensation

Note: Diagrams a, b
Relative P_{OO}, V_H, P_H to reference operation (RO)
f=5 Hz, rect. pulse D=62%

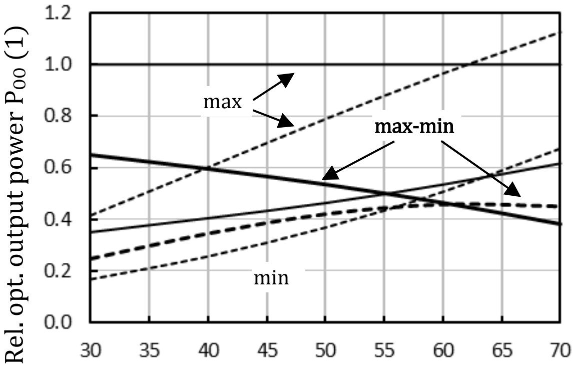
max: maximum value of P_{OO} response shape
min: minimum value of P_{OO} response shape
max-min: amplitude calculation of P_{OO} resp. shape

Fixed V_H: same voltage for all frequencies.

Compensated V_H: for every frequency value, the voltage is adjusted to achieve the same maximum of P_{OO} response shape as for 5 Hz.

■ Typical Timing Characteristics Pulse Duration D[1] (f = 50 Hz)

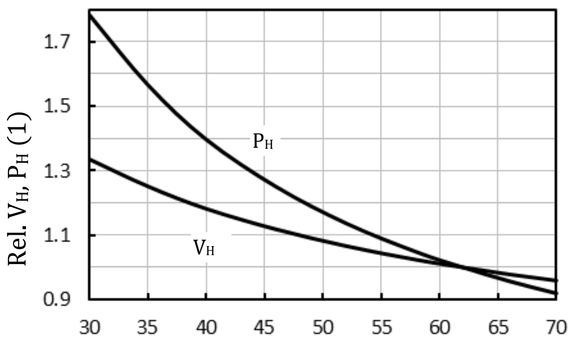
P_{OO} - - D (fixed V_H)
P_{OO} — D (compensated V_H)



Voltage pulse duration D (%)

Relative (to D=62%) max, min, max-min values of optical output power (P_{OO}) versus duty cycle D with fixed and compensated V_H

V_H, P_H — OD
(compensation factor)



Voltage pulse duration D (%)

Relative (to RO) electrical drive values heater voltage V_H and power P_H versus duty cycle D for compensation

Note: Diagrams a, b
Relative P_{OO}, V_H, P_H to reference operation (RO)
f=50 Hz, rect. voltage pulse

max: maximum value of P_{OO} response shape
min: minimum value of P_{OO} response shape
max-min: amplitude calculation of P_{OO} resp. shape

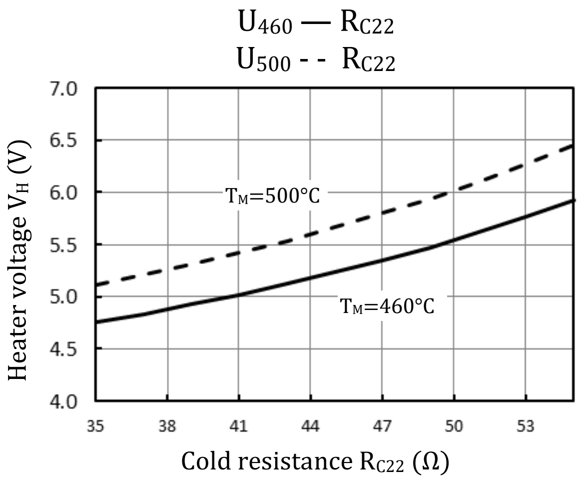
Fixed V_H: same voltage for all frequencies.

Compensated V_H: for every frequency value, the voltage is adjusted to achieve the same maximum of P_{OO} response shape as for D=62%.

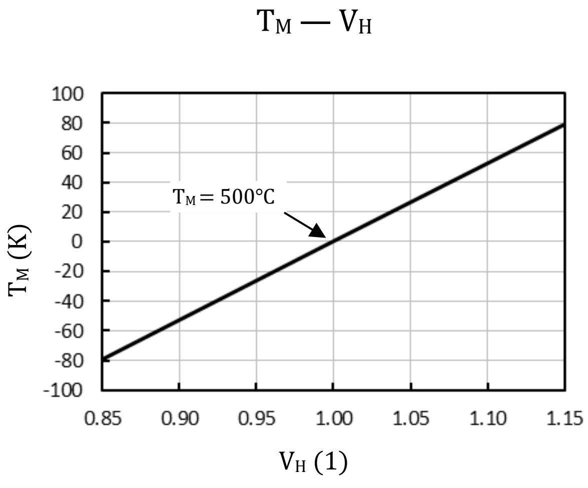
[1] Effective D shorter than 30% and voltage or power compensation at high frequencies (e.g. 20% @ 50 Hz) might impact the lifetime and characteristic of the devices because of additional stress in material layers.

■ Typical electrical/thermal characteristics (RO, T_A = 22°C)

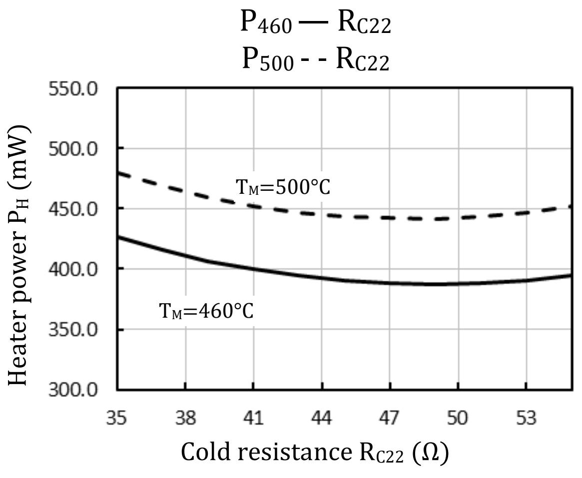
Parameter	Symbol	Rating	Unit
Peak chip membrane temperature	T_M	460/500	°C
Heater voltage	V_H	5.23/5.66	V
Heater power	P_H	394/446	mW



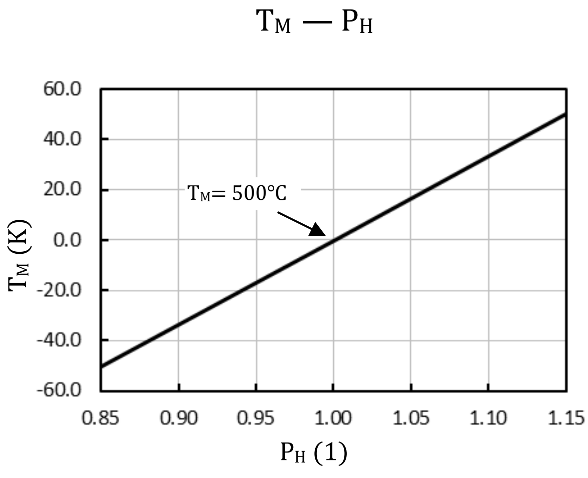
Mean[1] and upper bound of heater voltage V_H vs. cold resistance RC_{22}



Relative change of membrane temperature (T_M) by changing heater voltage (V_H)



Mean[1] and upper bound of heater power P_H vs. cold resistance RC_{22}

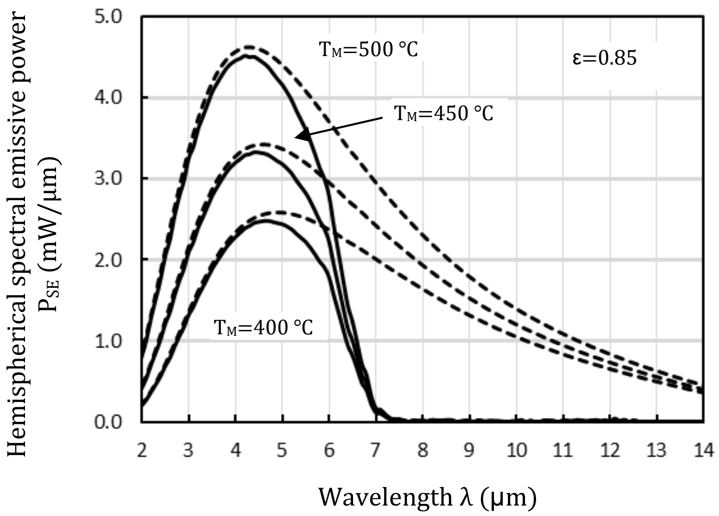


Relative change membrane temperature (T_M) by changing heater power (P_H)

[1] Recommended operation mode T_M =460°C, which ensures 95% confidence that the maximum temperature T_M = 500°C is not exceeded.

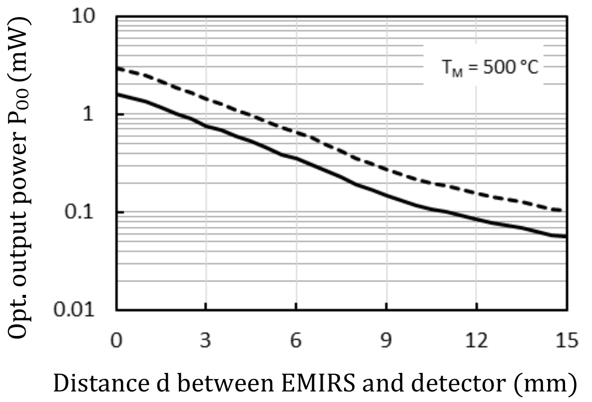
■ Typical Optical Characteristics (RO, T_A = 22°C)

$P_{SE, Sapphire}$ — λ / $P_{SE, BaF2}$ - - λ



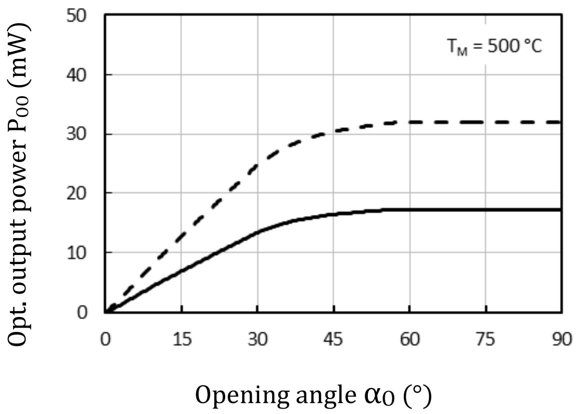
Hemispherical spectral emissive power of EMIRS200 chip surface with a typical emissivity (mean from 2 to 14 µm) of ε=0.85

$P_{OO, Sapphire}$ — d / $P_{OO, BaF2}$ - - d



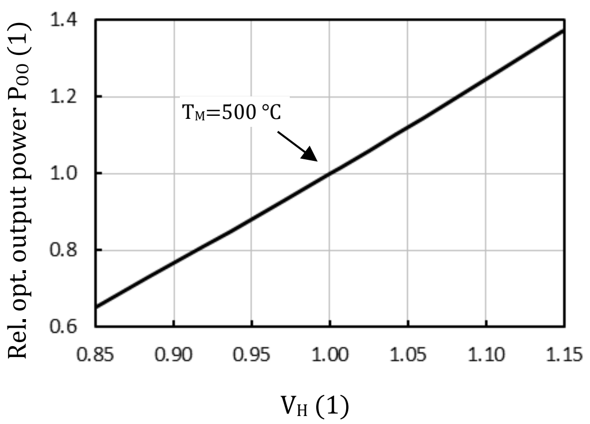
Optical output power (P_{OO}) versus distance d of a 1 mm² detection surface at 500°C T_M

$P_{SE, Sapphire}$ — α_O / $P_{SE, BaF2}$ - - α_O



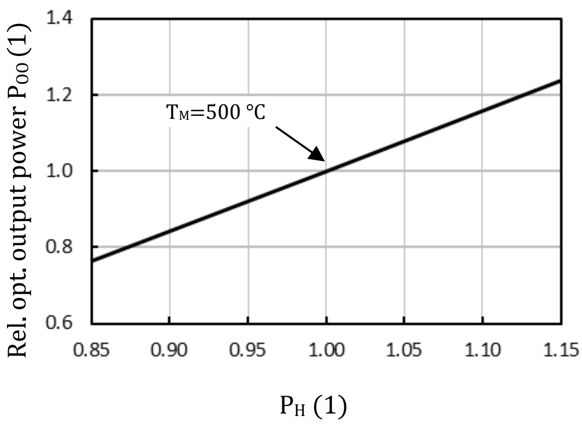
Optical output power (P_{OO}) versus opening angle α_O (integral rotation of a cone) at 500°C T_M

P_{OO} — V_H



Relative change of optical output power (P_{OO}) by changing heater voltage (V_H)

P_{OO} — P_H



Relative change of optical output power (P_{OO}) by changing heater power (P_H)